## NSN 5962-01-351-4990

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View Online at https://aerobasegroup.com/nsn/5962-01-351-4990				
Overall Length:				
1.060 inches				
Overall Height:				
0.400 inches				
Body Length:				
1.060 inches				
Body Width:				
Between 0.220 inches and 0.310 inches				
Body Height:				
Between 0.130 inches and 0.185 inches				
Maximum Power Dissipation Rating:				
2.0 watts				
Operating Tempurature Range:				
-55.0/+125.0 degrees celsius				
Storage Tempurature Range:				
-65.0/+150.0 degrees celsius				
End Application:				
Satellite communications terminal an/usc-3 (v) 1				
Features Provided:				
Programmed and monolithic and w/clock and bidirectional				
Inclosure Material:				
Ceramic				
Inclosure Configuration:				
Dual-in-line				
Output Logic Form:				
Transistor-transistor logic				
Input Circuit Pattern:				
16 input				
Case Outline Source And Designator:				
D-8 mil-m-38510				
Current Rating Per Characteristic:				
185.00 milliamperes reverse current, dc absolute				
Terminal Surface Treatment:				
Solder				
Product Name:				
And-or invert gate array				
Voltage Rating And Type Per Characteristic:				
-0.5 volts power source and 7.0 volts power source				
Time Rating Per Chacteristic:				
45.00 nanoseconds propagation delay time, high to low level output and 45.00 nanoseconds propagation delay time, low to high level				
output				
Memory Device Type:				

Pal

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Test	Data	Docum	ent
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96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

**Terminal Type And Quantity:** 

20 printed circuit

Shelf Life:

N/a

**Unit Of Measure:** 

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0